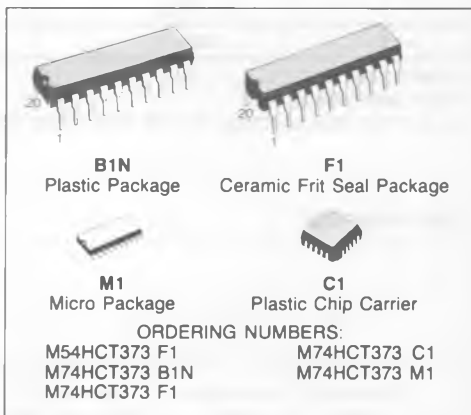


OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT

PRODUCT PREVIEW

- **LOW POWER DISSIPATION**
 $I_{CC} = 4 \mu A$ (MAX.) at $T_A = 25^\circ C$
- **COMPATIBLE WITH TTL OUTPUTS**
 $V_{IH} = 2 V$ (MIN) $V_{IL} = 0.8 V$ (MAX)
- **OUTPUT DRIVE CAPABILITY**
 15 LSTTL LOADS
- **SYMMETRICAL OUTPUT IMPEDANCE**
 $|I_{OH}| = I_{OL} = 6 mA$ (MIN.)
- **BALANCED PROPAGATION DELAYS**
 $t_{PLH} = t_{PHL}$
- **PIN AND FUNCTION COMPATIBLE**
 WITH 54/74LS373



DESCRIPTION

The M54/74HCT373 is a high speed CMOS OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

This 8-bit D-type latch is controlled by a latch enable input (LE) and an output enable input (OE). While the LE input is held high, the Q outputs will follow the data input precisely. When the LE is taken low, the Q outputs will be latched at the logic level of D input data.

While the OE input is low, the eight outputs will be in a normal logic state (high or low logic level) and while high level the outputs will be in a high impedance state.

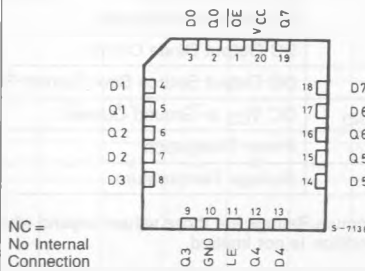
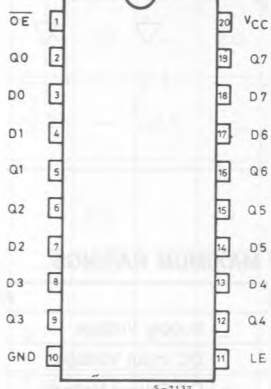
The three-state output configuration and the wide choice of outlines makes bus-organized system simple.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

This integrated circuit has totally compatible, input and output characteristics, with standard 54/74 LSTTL logic families.

M54HCT/74HCT devices are designed to directly interface HSC²MOS systems with TTL and NMOS components. These devices are also plug in replacements for LSTTL devices giving a reduction in power consumption.

PIN CONNECTIONS (top view)



TRUTH TABLE

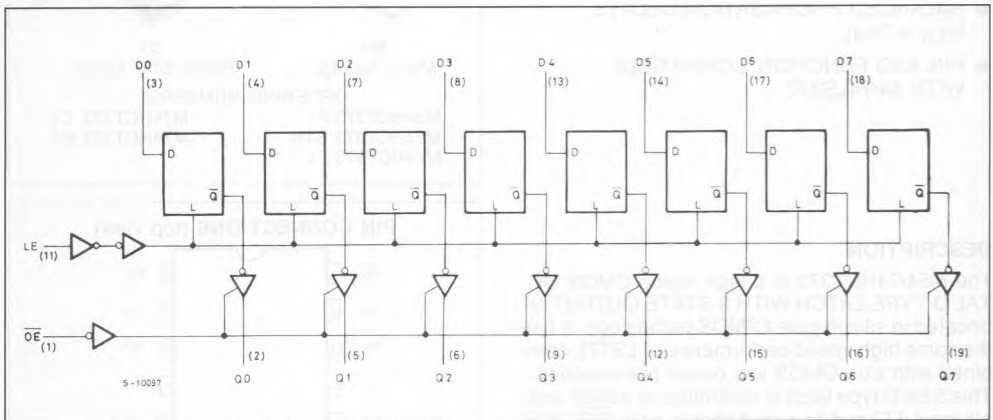
INPUTS			OUTPUTS
OE	LE	D	Q (HCT373)
H	X	X	Z
L	L	X	No change*
L	H	L	L
L	H	H	H

X: DON'T CARE

Z: HIGH IMPEDANCE

*: Q OUTPUT WAS LATCHED AT THE TIME WHEN THE LE INPUT IS TAKEN LOW LOGIC LEVEL.

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	- 0.5 to 7	V
V _I	DC Input Voltage	- 0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	- 0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 35	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 70	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	- 65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_A	Operating Temperature	74HC Series - 40 to 85 54HC Series - 55 to 125	°C
t_r, t_f	Input Rise and Fall Time	0 to 500	ns

DC SPECIFICATIONS

Symbol	Parameter	V_{CC}	Test Condition	$T_A = 25^\circ\text{C}$ 54HC and 74HC			-40 to 85°C 74HC		-55 to 125°C 54HC		Unit	
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
V_{IH}	High Level Input Voltage	4.5 to 5.5		2.0	—	—	2.0	—	2.0	—	V	
V_{IL}	Low Level Input Voltage	4.5 to 5.5		—	—	0.8	—	0.8	—	0.8	V	
V_{OH}	High Level Output Voltage	4.5	V_{IN}	I_{OH} - 20 μA	4.4	4.5	—	4.4	—	4.4	—	V
			V_{IH} or V_{IL}									
V_{OL}	Low Level Output Voltage	4.5	V_{IN}	I_{OL} 20 μA	—	0.0	0.1	—	0.1	—	0.1	V
			V_{IH} or V_{IL}									
I_{OZ}	3-State Output Off-State Current	5.5	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	—	—	± 0.5	—	± 5.0	—	± 10.0		
I_{IN}	Input Leakage Current	5.5	$V_{IN} = V_{CC}$ or GND	—	—	± 0.1	—	± 1	—	± 1	μA	
I_{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND	—	—	4	—	40	—	80	μA	
I_{CC}			Per input: $V_{IN} = 0.5\text{V}$ or 2.4V Other input: V_{CC} or GND	—	—	2.0	—	2.9	—	3.0	mA	

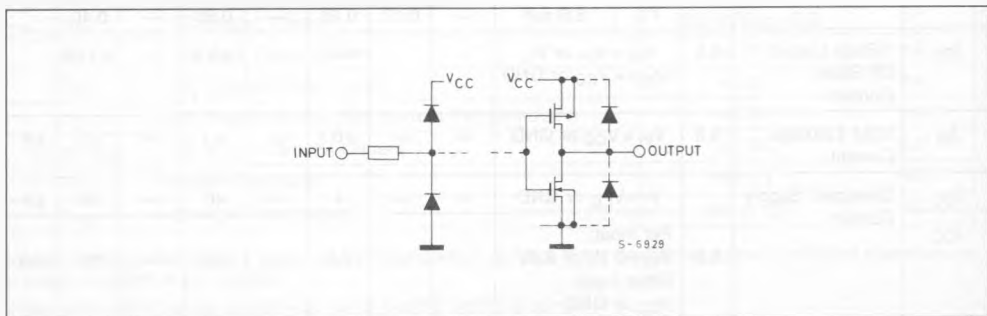
AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

Symbol	Parameter	V_{CC}	Test Condition	$T_A = 25^\circ\text{C}$ 54HC and 74HC			-40 to 85°C 74HC		-55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	4.5		—	7	12	—	15	—	19	ns
t_{PLH} t_{PHL}	Propagation Delay Time (LE-Q)	4.5		—	23	35	—	44	—	53	ns
t_{PLH} t_{PHL}	Propagation Delay Time (D-Q)	4.5		—	23	35	—	44	—	53	ns
$t_{W(H)}$	Minimum Pulse Width (LE)	4.5		—	8	15	—	19	—	22	ns
t_s	Minimum Set-up Time	4.5		—	0	5	—	6	—	8	ns
t_h	Minimum hold Time	4.5		—	3	10	—	13	—	15	ns
t_{PZH} t_{PZL}	3-State Output Enable Time	4.5	$R_L = 1\text{k}\Omega$	—	23	35	—	44	—	53	ns
t_{PLZ} t_{PHZ}	3-State Output Disable Time	4.5	$R_L = 1\text{k}\Omega$	—	21	30	—	38	—	45	ns
C_{IN}	Input Capacitance			—	5	10	—	10	—	10	pF
C_{OUT}	Output Capacitance			—	10	—	—	—	—	—	pF
$C_{PD} (*)$	Power Dissipation Capacitance			—	55	—	—	—	—	—	pF

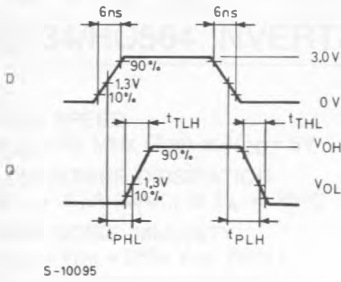
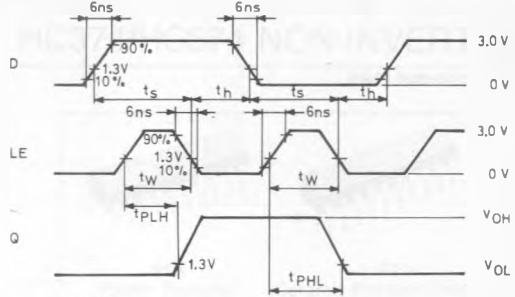
Note (*) C_{PD} is defined as the value of IC's internal equivalent capacitance which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current is: $I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per Latch)

INPUT AND OUTPUT EQUIVALENT CIRCUIT



SWITCHING CHARACTERISTICS TEST WAVEFORM

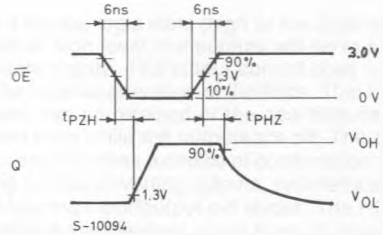
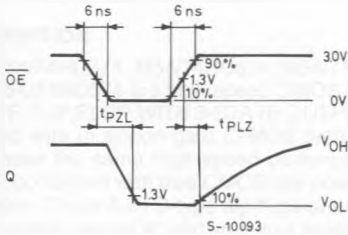
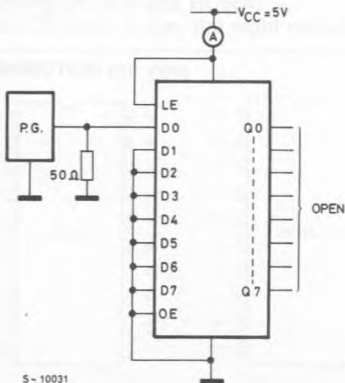
 $t_{PLH}, t_{PHL} (D-Q)$  $t_{PLH}, t_{PHL} (LE-Q), t_s, t_h, t_w$  t_{PLZ}, t_{PZL}

The 1kΩ load resistors should be connected between outputs and V_{CC} line and the 50pF load capacitors should be connected between outputs and GND line. All inputs except \overline{OE} input should be connected to V_{CC} line to GND line such that outputs will be in low logic level while \overline{OE} input is held low.

 t_{PHZ}, t_{PHL}

The 1kΩ load resistors and the 50pF load capacitors should be connected between each outputs and GND line.

All inputs except \overline{OE} input should be connected to V_{CC} or GND line such that output will be in high logic level while \overline{OE} input is held low.

TEST CIRCUIT I_{CC} (Opr.)

INPUT WAVEFORM

